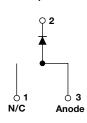
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 16 A



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LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)} 16 A					
V _R	1200 V				
V _F at I _F	2.3 V				
t _{rr} (typ.)	30 ns				
T _J max.	150 °C				
Package D ² PAK (TO-263AB)					
Circuit configuration Single					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
 FREE
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA16TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

MECHANICAL DATA

Case: D²PAK (TO-263AB) Molding compound meets UL 94 V-0 flammability rating **Terminal:** matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Cathode to anode voltage	V _R		1200	V			
Maximum continuous forward current	I _F	T _C = 100 °C	16				
Single pulse forward current	I _{FSM}		190	А			
Maximum repetitive forward current	I _{FRM}		64				
Maximum power dissipation	P _D	T _C = 25 °C	151	W			
		T _C = 100 °C	60	vv			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			

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ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		1200	-	-	
Maximum forward voltage		I _F = 16 A		-	2.5	3.0	V
	V _{FM}	I _F = 32 A	See fig. 1	-	3.2	3.93	
		I _F = 16 A, T _J = 125 °C		-	2.3	2.7	
Maximum reverse		$V_{R} = V_{R}$ rated	See fig. 2	-	0.75	20	
leakage current	IRM	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$ See fig. 2		-	375	2000	μA
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	27	40	pF
Series inductance	L _S	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ J}$	A/μs, V _R = 30 V	-	30	-		
Reverse recovery time See fig. 5 and 10	t _{rr1}	T _J = 25 °C		-	90	135	ns	
	t _{rr2}	T _J = 125 °C		-	164	245		
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 16 A dI _F /dt = 200 A/μs V _R = 200 V	-	5.8	10	А	
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.3	15	A	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	260	675	nC	
See fig. 7	Q _{rr2}	T _J = 125 °C		-	680	1838	ne	
Peak rate of fall of recovery current during t _b See fig. 8	dl _{(rec)M} /dt1	T _J = 25 °C		-	120	-		
	dl _{(rec)M} /dt2	T _J = 125 °C		-	76	-	A∕µs	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction-to-case	R _{thJC}		-	-	0.83	K/W		
Thermal resistance, junction-to-ambient	R _{thJA}	Typical socket mount	-	-	80	r∨ vv		
Waight			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Marking device		Case style D ² PAK (TO-263AB)		HFA16	TB120S	•		



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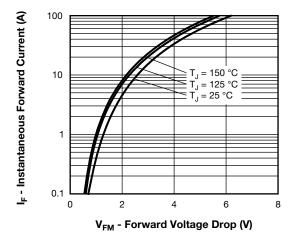


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

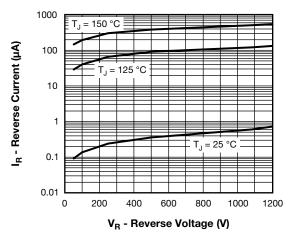


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

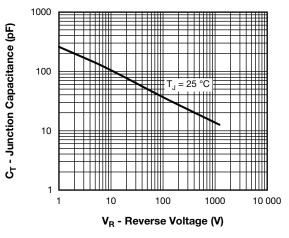
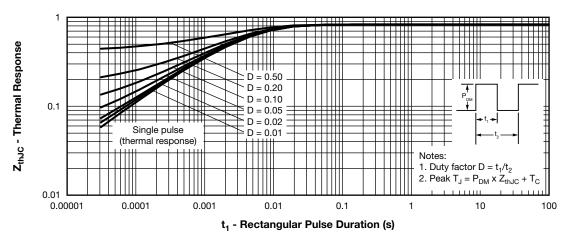


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)





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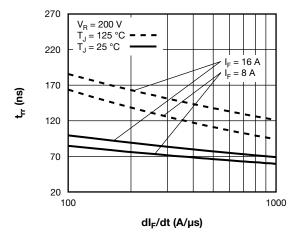


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

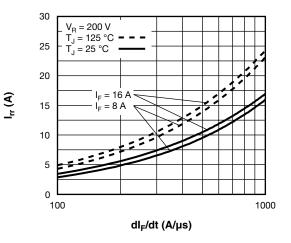


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

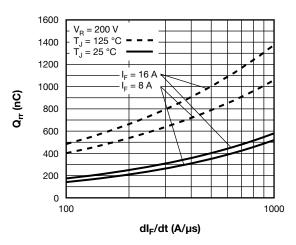


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

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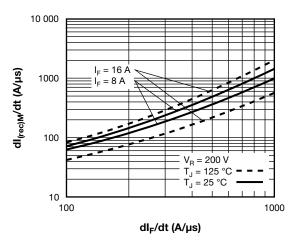


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)

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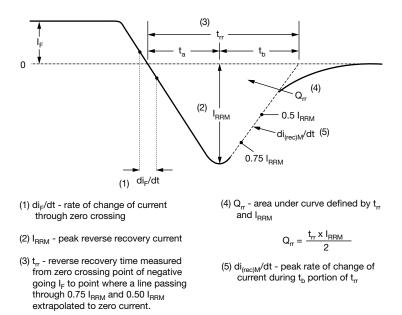
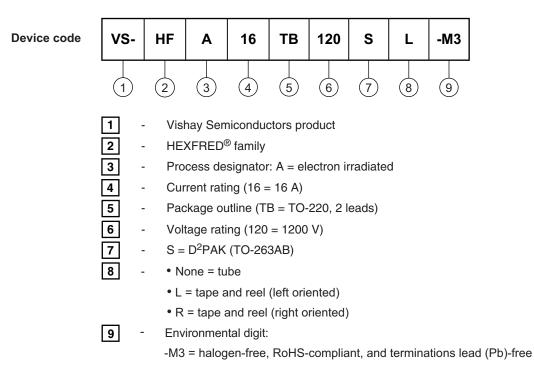


Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE





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ORDERING INFORMATION (Example)							
PREFERRED P/N	PACKAGING DESCRIPTION						
VS-HFA16TB120S-M3	50	Antistatic plastic tube					
VS-HFA16TB120SR-M3	800	13" diameter reel					
VS-HFA16TB120SL-M3	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?96164					
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				

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D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INCHES		NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INCHES		NOTES	
STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100 BSC			
Н	14.61	15.88	0.575	0.625		
L	1.78	2.79	0.070	0.110		
L1	-	1.65	-	0.066	3	
L2	1.27	1.78	0.050	0.070		
L3	0.25 BSC		0.010	BSC		
L4	4.78	5.28	0.188	0.208		

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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